





SOT-23 Formed SMD Package

BCX70G BCX70H BCX70J BCX70K

SILICON PLANAR EPITAXIAL TRANSISTORS

N-P-N silicon transistors

Marking

BCX70G = AG

BCX70H = AH

BCX70J = AJ

BCX70K = AK

Pin configuration

1 = BASE

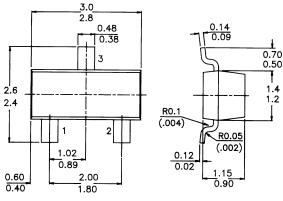
2 = EMITTER

3 = COLLECTOR





PACKAGE OUTLINE DETAILS



ABSOLUTE MAXIMUM RATINGS

Collector–emitter voltage $(V_{BE} = 0)$	V_{CES}	max.	45 V
Collector–emitter voltage (open base)	V_{CE0}	max.	45 V
Collector current (d.c.)	I_C	max.	200 mA
Total power dissipation at $T_{amb} = 25$ °C	P_{tot}	max.	250 mW
Junction temperature	T_j	max.	150 ° C
Transition frequency at $f = 100 \text{ MHz}$,		
$V_{CE} = 5 \ V; I_C = 10 \ mA$	f_T	typ.	250 MHz
Noise figure at f: 1 kHz			
$V_{CE} = 5 \text{ V; } I_{C:} 200 \text{ mA; } B = 200 \text{ Hz}$	F	typ.	2 dB
RATINGS (at $T_A = 25^{\circ}\text{C}$ unless otherwise specified)			

Limiting values

Collector–emitter voltage ($V_{BE} = 0$)	V_{CES}	max.	45 V
Collector-emitter voltage (open base)	V_{CE0}	max.	45 V
Emitter-base voltage (open collector)	V_{EBO}	max.	5 V

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Collector current (d.c.)				I_C	max.	200	mA
Base current				$l_{\rm B}$	max.		mA
Total power dissipation up to $T_{amb} = 2$	25 °C			P_{tot}	max.	250	mW
Storage temperature				T_{stg}	–55 to		
Junction temperature				T_j	max.	150	$^{\circ}$ C
THERMAL RESISTANCE				,			
From junction to ambient				R., .	_	500	KW.
from junction to umown				R _{th j} —a	=	300	1444
CHARACTERISTICS							
T _{amb} : 25 °C unless otherwise specified							
Collector–emitter cut–off current							
$V_{BE} = 0; V_{CE} = 45 V$				I_{CES}	<		пA
$V_{BE} = 0; V_{CE} = 45 \ V; T_{amb} = 150$	°C			I_{CES}	<	20	mA
Emitter-base cut-off current						20	
$I_C = 0; V_{EB} = 4 V$				I_{EBO}	<	20	пA
Saturation voltages				17	0.05 1-	0.25	17
at $I_C = 10 \text{ mA}$; $I_B = 0.25 \text{ mA}$					0,05 to		
				V_{BEsat}			
at $I_C = 50 \text{ mA}$; $I_B = 1,25 \text{ mA}$				V_{CEsat}	0,1 to		
				V_{BEsat}	0,7 to		
Transition frequency at $f = 100 \text{ MHz}$ D					>	125	
$I_C = 10 \text{ mA}; V_{CE} = 5 \text{ V}$				f_T	typ.	250	MHz
Collector capacitance at $f = 1$ MHz				0	,	2.5	r
$I_E = I_e = 0$; $V_{CB} = 10 \text{ V}$				C_c	typ.	2,5	рь
Emitter capacitance at $f = 1$ MHz $I_C = I_c = 0$; $V_{EB} = 0.5$ V				C_e	ta can	0	пΓ
Noise figure at $R_S = 2 kW$,				Ce	typ.		pF dB
$I_C = 200 \text{ mA}; V_{CE} = 5 \text{ V}; f = 1 \text{ kHz};$	B - 200	H~		F	typ. <		d B
1C = 200 mu, $VCE = 3 V, j = 1 K112,$	D = 200	112		1		U	иЪ
		I.	BCX70G	70H	70J	70K	
D.C. current gain	1			10	20	100	
$V_{CE} = 5V$; $lC = 10$ m A $V_{CE} = 5$ V ; $I_{C} = 2$ mA	h_{FE}	> >		$\begin{vmatrix} 40 \\ 180 \end{vmatrix}$	30 250	100 380	
VCE = 3 V, 1C = 2 mH	"FE	<	220	310	460	630	
$V_{CE} = 1 \ V; \ I_C = 50 \ mA$	h_{FE}	>	50	70	90	100	
	"FE		50	'		100	
Small-signal current gain		>	125	175	250	350	
$V_{CE} = 5 V$; $IC = 2 mA$; $f = 1 kHz$	hfe	<	250	350	500	700	
Output admittance							
$V_{CE} = 5 \text{ V}; IC = 2 \text{ mA}; f = 1 \text{ kHz}$	hoe	typ.	18	24	30	50	mS
Base-emitter voltage	1100	igp.					
$V_{CE} = 5 V; I_C = 2 mA$	V_{BE}			0,5	55 to 0.7	75	V
· CE = 0 v, 1C = 2 m21	* DE	typ.			0,65		V
$V_{CE} = 5 \ V; I_{C} = 10 \ \text{mA}$	V_{BE}	typ.			0,52		V
$V_{CE} = 1 \text{ V; } I_C = 50 \text{ mA}$	V_{BE}	typ.			0,78		V
· CL 2 · / 10 00	· DE	.34.			٥,, ٥		•

Notes

Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Discrete Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished on the CDIL Web Site/CD is believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Discrete Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

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